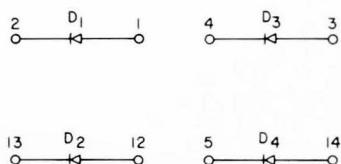


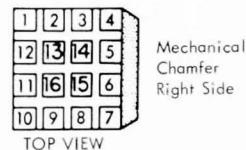
Functional Description

The Eight Single Diodes, ESD-1A, module consists of eight individual diodes with the anode and cathode terminating at specific pins. The individual diodes offer the circuit designer a uniformity of circuit packaging with other SLT modules and the additional design flexibility his application may require. The ESD-1A SLT diodes can be used for clamps and AND extending.

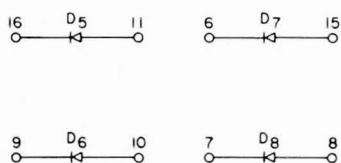
Schematic



Terminal Configuration



NOTE - 16 PIN MODULE



Maximum Ratings

Maximum current = 5.0 millamps
Breakdown Voltage = 13 Volts

ESD-1A Module Functional Tests

INDIVIDUAL DEVICE PARAMETER TESTS						
TESTS	COMPONENTS	TESTS CONDITIONS	T °C	LIMITS		UNITS
				MIN	MAX	
Q_S	$D_1 - D_8$	$I_F = 3.0\text{ma}$ See Fig. 1	25		.23	PC
FWD RECOVERY PEAK AMPLITUDE	$D_1 - D_8$	$I_F = 2.0\text{ma}$ See Fig. 2	25		.085	V
V_F	$D_1 - D_8$	$I_F = 0.1\text{ma}$	25	.51		V
V_F	$D_1 - D_8$	$I_F = 0.5\text{ma}$	25	.58		V
V_F	$D_1 - D_8$	$I_F = 1.0\text{ma}$	25	.61		V
V_F	$D_1 - D_8$	$I_F = 3.0\text{ma}$	25		.84	V
V_F	$D_1 - D_8$	$I_F = 5.0\text{ma}$	25		.87	V
BV_R	$D_1 - D_8$	$I_R = 10\ \mu\text{a}$	25	13		V
I_R	$D_1 - D_8$	$V_R = 12V$	75		0.5	μa
DIODE CAPACITANCE	$D_1 - D_8$	OV BIAS, $f = 1 \pm 0.5\text{mhz}$ AC SIGNAL $\leq 50\text{mv P-P}$	25		3.5	pf

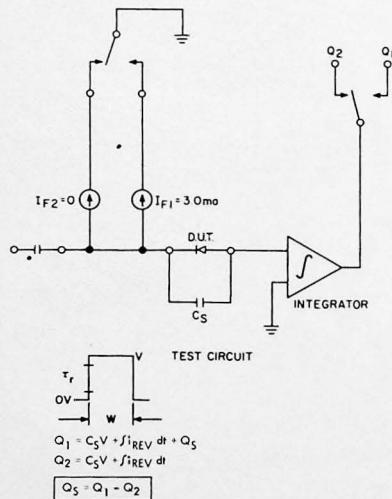


FIGURE 1

Notes

For this test the diode shunt capacity (incl Probe) shall be $10.5 \pm \text{pf}$ with a 50Ω HF Resistor in place of the Diode, the rise time, t_r , of the input voltage wave form shall be $\leq 2\text{ ns}$, the operating frequency $\leq 50\text{KHz}$, pulse width $\leq 50\text{ns}$, Bandwidth of detector $\geq 750\text{MHz}$. Turn on is from $V_F = 0$.

Store Charge Test

V-PULSE AMPLITUDE: $5V \pm 25\%$

W-PULSE WIDTH: $> 50\text{ns}$

RISE TIME: $1\% - 50\% < 0.5\text{ns}$

$10\%-90\% < 0.4\text{ns}$

SOURCE IMPEDANCE $< 10\ \text{OHMS}$

$|I_{F1}|$ - FORWARD CURRENT = $3.0\text{ma} \pm 0.3\%$

$|I_{F2}|$ - FORWARD CURRENT = 0ma

C_S - SHUNT CAPACITY $< 5\ \text{pf}$

INTEGRATOR RESPONSE $\leq 1\text{ns}$

Q1 - CHARGE WHEN D.U.T. IS FORWARD BIASED WITH $I_{F1} = 3.0\text{ma}$

Q2 - CHARGE WHEN D.U.T. IS FORWARD BIASED WITH $I_{F2} = 0\text{ma}$

Q_S - STORED CHARGE

$|I_{REV}|$ - DIODE LEAKAGE CURRENT

Forward Recovery

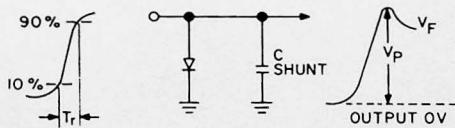


FIGURE 2